

### FEATURES

**44 V supply maximum ratings**

**$V_{SS}$  to  $V_{DD}$  analog signal range**

**Low on resistance (45  $\Omega$  max)**

**Low  $\Delta R_{ON}$  (5  $\Omega$  max)**

**Low  $R_{ON}$  match (4  $\Omega$  max)**

**Low power dissipation**

**Fast switching times**

$t_{ON} < 175$  ns

$t_{OFF} < 145$  ns

**Low leakage currents (5 nA max)**

**Low charge injection (10 pC max)**

**Break-before-make switching action**

### APPLICATIONS

**Audio and video switching**

**Battery-powered systems**

**Test equipment**

**Communication systems**

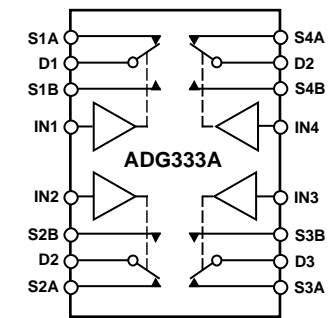
### GENERAL DESCRIPTION

The ADG333A is a monolithic CMOS device comprising four independently selectable SPDT switches. It is designed on an LC<sup>2</sup>MOS process, which provides low power dissipation yet achieves a high switching speed and a low on resistance.

The on resistance profile is very flat over the full analog input range, ensuring good linearity and low distortion when switching audio signals. High switching speed also makes the part suitable for video signal switching. CMOS construction ensures ultralow power dissipation, making the part ideally suited for portable, battery-powered instruments.

When they are on, each switch conducts equally well in both directions and has an input signal range that extends to the power supplies. In the off condition, signal levels up to the supplies are blocked. All switches exhibit break-before-make switching action for use in multiplexer applications. Inherent in the design is low charge inject

### FUNCTIONAL BLOCK DIAGRAM



SWITCHES SHOWN FOR A LOGIC 1 INPUT

Figure 1.

01212-001

### PRODUCT HIGHLIGHTS

1. Extended signal range.  
The ADG333A is fabricated on an enhanced LC<sup>2</sup>MOS process, giving an increased signal range which extends to the supply rails.
2. Low power dissipation.
3. Low  $R_{ON}$ .
4. Single-supply operation.  
For applications where the analog signal is unipolar, the ADG333A can be operated from a single rail power supply. The part is fully specified with a single 12 V supply.

Rev. A

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## REVISION HISTORY

### 3/05—Rev. 0 to Rev. A

Updated Format.....	Universal
Changes to Specifications Tables.....	3
Updated Outline Dimensions .....	12
Changes to Ordering Guide .....	12

### 10/95—Revision 0: Initial Version

## SPECIFICATIONS

### DUAL SUPPLY

$V_{DD} = +15\text{ V}$ ,  $V_{SS} = -15\text{ V}$ ,  $GND = 0\text{ V}$ , unless otherwise noted.<sup>1</sup>

**Table 1.**

Parameter	+25°C	-40°C to +85°C	Unit	Test Conditions/Comments
<b>ANALOG SWITCH</b>				
Analog Signal Range		$V_{SS}$ to $V_{DD}$	V	
$R_{ON}$	20		$\Omega$ typ	$V_D = \pm 10\text{ V}$ , $I_S = -1\text{ mA}$
	45	45	$\Omega$ max	
$\Delta R_{ON}$		5	$\Omega$ max	$V_D = \pm 5\text{ V}$ , $I_S = -10\text{ mA}$
$R_{ON}$ Match		4	$\Omega$ max	$V_D = \pm 10\text{ V}$ , $I_S = -10\text{ mA}$
<b>LEAKAGE CURRENTS</b>				
Source OFF Leakage $I_S$ (OFF)	$\pm 0.1$		nA typ	$V_{DD} = +16.5\text{ V}$ , $V_{SS} = -16.5\text{ V}$
	$\pm 0.25$	$\pm 3$	nA max	$V_D = \pm 15.5\text{ V}$ , $V_S = +15.5\text{ V}$
Channel ON Leakage $I_D$ , $I_S$ (ON)	$\pm 0.1$		nA typ	Figure 15
	$\pm 0.4$	$\pm 5$	nA max	$V_S = V_D = \pm 15.5\text{ V}$
				Figure 16
<b>DIGITAL INPUTS</b>				
Input High Voltage, $V_{INH}$		2.4	V min	
Input Low Voltage, $V_{INL}$		0.8	V max	
Input Current				
$I_{INL}$ or $I_{INH}$		$\pm 0.005$	$\mu\text{A}$ typ	$V_{IN} = 0\text{ V}$ or $V_{DD}$
		$\pm 0.5$	$\mu\text{A}$ max	
<b>DYNAMIC CHARACTERISTICS<sup>2</sup></b>				
$t_{ON}$	90		ns typ	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$ ;
		175	ns max	$V_S = \pm 10\text{ V}$ ; Figure 17
$t_{OFF}$	80		ns typ	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$ ;
		145	ns max	$V_S = \pm 10\text{ V}$ ; Figure 17
Break-Before-Make Delay, $t_{OPEN}$	10		ns min	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$ ;
				$V_S = +5\text{ V}$ ; Figure 18
Charge Injection	2		pC typ	$V_D = 0\text{ V}$ , $R_D = 0\ \Omega$ , $C_L = 10\text{ nF}$ ;
	10		pC max	$V_{DD} = +15\text{ V}$ , $V_{SS} = -15\text{ V}$ ; Figure 19
OFF Isolation	72		dB typ	$R_L = 75\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ;
				$V_S = 2.3\text{ V rms}$ ; Figure 20
Channel-to-Channel Crosstalk	85		dB typ	$R_L = 75\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ;
				$V_S = 2.3\text{ V rms}$ ; Figure 21
$C_S$ (OFF)	7		pF typ	
$C_D$ , $C_S$ (ON)	26		pF typ	
<b>POWER REQUIREMENTS</b>				
$I_{DD}$	0.05		mA typ	Digital inputs = 0 V or 5 V
	0.25	0.35	mA max	
$I_{SS}$	0.01		$\mu\text{A}$ typ	
	1	5	$\mu\text{A}$ max	
$V_{DD}/V_{SS}$		$\pm 3/\pm 20$	V min/V max	$ V_{DD}  =  V_{SS} $

<sup>1</sup> Temperature range is as follows: B version:  $-40^\circ\text{C}$  to  $+85^\circ\text{C}$ .

<sup>2</sup> Guaranteed by design; not subject to production test.

# ADG333A

## SINGLE SUPPLY

$V_{DD} = +12\text{ V}$ ,  $V_{SS} = 0\text{ V} \pm 10\%$ ,  $GND = 0\text{ V}$ , unless otherwise noted.<sup>1</sup>

Table 2.

Parameter	+25°C	-40°C to +85°C	Unit	Test Conditions/Comments
<b>ANALOG SWITCH</b>				
Analog Signal Range		0 V to $V_{DD}$	V	
RON	35	75	$\Omega$ typ $\Omega$ max	$V_D = 1\text{ V}$ , $10\text{ V}$ , $I_S = -1\text{ mA}$
<b>LEAKAGE CURRENTS</b>				
Source OFF Leakage $I_S$ (OFF)	$\pm 0.1$ $\pm 0.25$	$\pm 3$	nA typ nA max	$V_{DD} = 13.2\text{ V}$ $V_D = 12.2\text{ V}/1\text{ V}$ , $V_S = 1\text{ V}/12.2\text{ V}$ Figure 15
Channel ON Leakage $I_D$ , $I_S$ (ON)	$\pm 0.1$ $\pm 0.4$	$\pm 5$	nA typ nA max	$V_S = V_D = 12.2\text{ V}/1\text{ V}$ Figure 16
<b>DIGITAL INPUTS</b>				
Input High Voltage, $V_{INH}$		2.4	V min	
Input Low Voltage, $V_{INL}$		0.8	V max	
Input Current $I_{INL}$ or $I_{INH}$		$\pm 0.005$ $\pm 0.5$	$\mu\text{A}$ typ $\mu\text{A}$ max	$V_{IN} = 0\text{ V}$ or $V_{DD}$
<b>DYNAMIC CHARACTERISTICS<sup>2</sup></b>				
$t_{ON}$	110	200	ns typ ns max	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$ ; $V_S = 8\text{ V}$ ; Figure 17
$t_{OFF}$	100	180	ns typ ns max	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$ ; $V_S = 8\text{ V}$ ; Figure 17
Break-Before-Make Delay, $t_{OPEN}$	10		ns min ns min	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$ ; $V_S = 5\text{ V}$ ; Figure 18
Charge Injection	5		pC typ	$V_D = 6\text{ V}$ , $R_D = 0\text{ W}$ , $C_L = 10\text{ nF}$ ; $V_{DD} = 12\text{ V}$ , $V_{SS} = 0\text{ V}$ ; Figure 19
OFF Isolation	72		dB typ	$R_L = 75\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ; $V_S = 1.15\text{ V rms}$ ; Figure 20
Channel-to-Channel Crosstalk	85		dB typ	$R_L = 75\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ; $V_S = 1.15\text{ V rms}$ ; Figure 21
$C_S$ (OFF)	12		pF typ	
$C_D$ , $C_S$ (ON)	25		pF typ	
<b>POWER REQUIREMENTS</b>				
$I_{DD}$	0.05 0.25	0.35	mA typ mA max	$V_{DD} = 13.5\text{ V}$ Digital inputs = 0 V or 5 V
$V_{DD}$		$\pm 3/\pm 30$	V min/V max	

<sup>1</sup> Temperature range is as follows: B Version: -40°C to +85°C.

<sup>2</sup> Guaranteed by design; not subject to production test.

## ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$  unless otherwise noted.

**Table 3.**

Parameter	Min
$V_{DD}$ to $V_{SS}$	+44 V
$V_{DD}$ to GND	-0.3 V to +30 V
$V_{SS}$ to GND	+0.3 V to -30 V
Analog, Digital Inputs <sup>1</sup>	$V_{SS} - 2\text{ V}$ to $V_{DD} + 2\text{ V}$ or 20 mA, whichever occurs first
Continuous Current, S or D	20 mA
Peak Current, S or D (Pulsed at 1 ms, 10% Duty Cycle Max)	40 mA
Operating Temperature Range Industrial (B Version)	-40°C to +85°C
Storage Temperature Range	-65°C to +125°C
Junction Temperature	150°C
$\theta_{JA}$ , Thermal Impedance	
PDIP Package	103°C/W
SOIC Package	74°C/W
SSOP Package	130°C/W
Lead Temperature, Soldering (10 sec)	260°C
Lead Temperature, Soldering Vapor Phase (60 sec)	215°C
Infrared (15 sec)	220°C
Lead Temperature, Soldering Vapor Phase (60 sec)	215°C
Infrared (15 sec)	220°C

<sup>1</sup> Overvoltage at IN, S, or D is clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**Table 4. Truth Table**

Logic	Switch A	Switch B
0	Off	On
1	On	Off

### ESD CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



## TERMINOLOGY

### $R_{ON}$

Ohmic resistance between D and S.

### $\Delta R_{ON}$

$R_{ON}$  variation due to a change in the analog input voltage with a constant load current.

### $R_{ON}$ Match

Difference between the  $R_{ON}$  of any two channels.

### $I_S$ (OFF)

Source leakage current with the switch off.

### $I_D$ (OFF)

Drain leakage current with the switch off.

### $I_D, I_S$ (ON)

Channel leakage current with the switch on.

### $V_D$ ( $V_S$ )

Analog voltage on Terminals D, S.

### $C_S$ (OFF)

OFF switch source capacitance.

### $C_D$ (OFF)

OFF switch drain capacitance.

### $C_D, C_S$ (ON)

ON switch capacitance.

### $t_{ON}$

Delay between applying the digital control input and the output switching on.

### $t_{OFF}$

Delay between applying the digital control input and the output switching off.

### $t_{OPEN}$

Break-before-make delay when switches are configured as a multiplexer.

### $V_{INL}$

Maximum input voltage for Logic 0.

### $V_{INH}$

Minimum input voltage for Logic 1.

### $I_{INL}$ ( $I_{INH}$ )

Input current of the digital input.

### Crosstalk

A measure of unwanted signal which is coupled through from one channel to another as a result of parasitic capacitance.

### Off Isolation

A measure of unwanted signal coupling through an OFF switch.

### Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching.

## PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

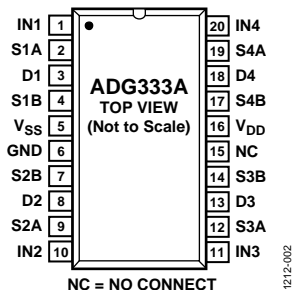


Figure 2. PDIP Pin Configuration

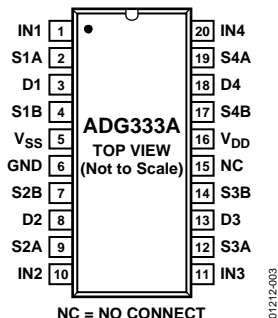


Figure 3. SOIC Pin Configuration

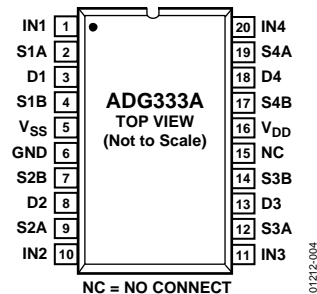


Figure 4. SSOP Pin Configuration

Table 5. Pin Function Descriptions

Pin No.	Mnemonic	Description
1, 10, 11, 20	IN1, IN2, IN3, IN4	Logic Control Input.
2, 4, 7, 9, 12, 14, 17, 19	S1A, S1B, S2B, S2A, S3A, S3B, S4B, S4A	Source Terminal. Can be an input or output.
3, 8, 13, 18	D1, D2, D3, D4	Drain Terminal. Can be an input or output.
5	V <sub>SS</sub>	Most Negative Power Supply Potential in Dual Supplies. In single-supply applications, it can be connected to ground.
6	GND	Ground (0 V) Reference.
15	NC	No Connect.
16	V <sub>DD</sub>	Most Positive Power Supply Potential.

## TYPICAL PERFORMANCE CHARACTERISTICS

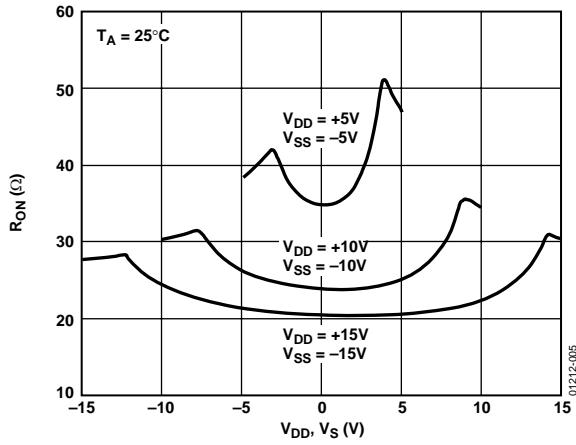


Figure 5.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ): Dual Supply

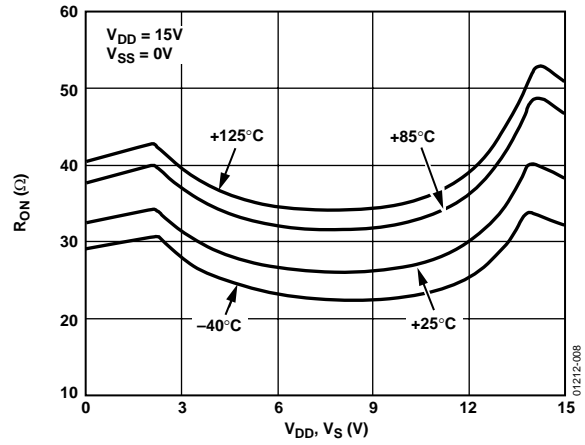


Figure 8.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures: Single Supply

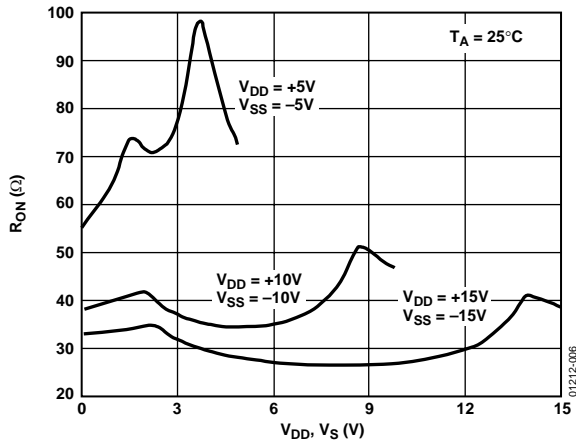


Figure 6.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ): Single Supply

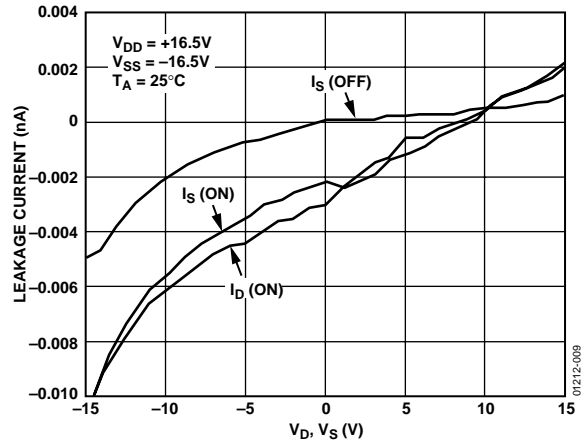


Figure 9. Leakage Currents as a Function of  $V_D$  ( $V_S$ ): Dual Supply

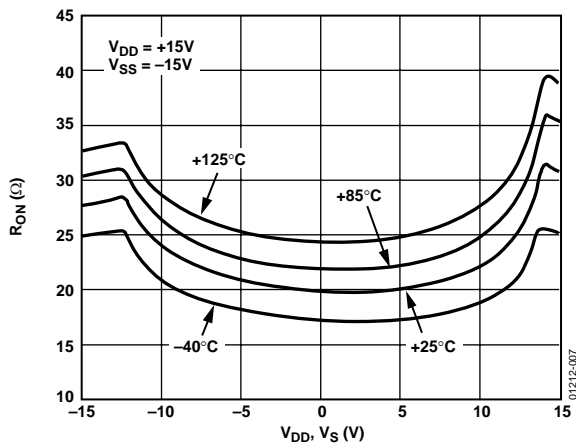


Figure 7.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures: Dual Supply

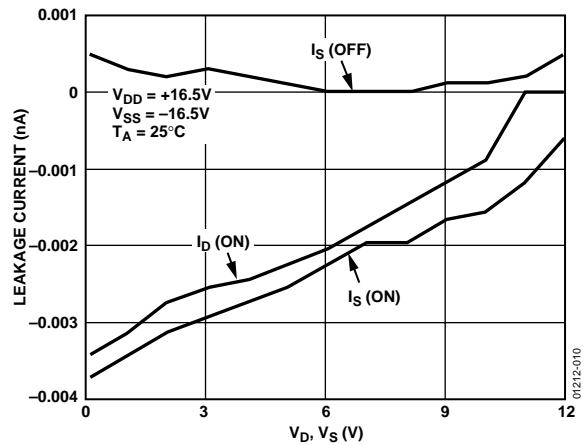


Figure 10. Leakage Currents as a Function of  $V_D$  ( $V_S$ ): Single Supply



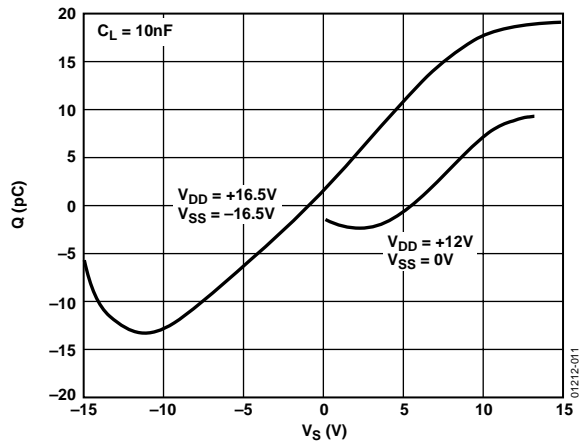


Figure 11. Charge Injection as a Function of  $V_S$

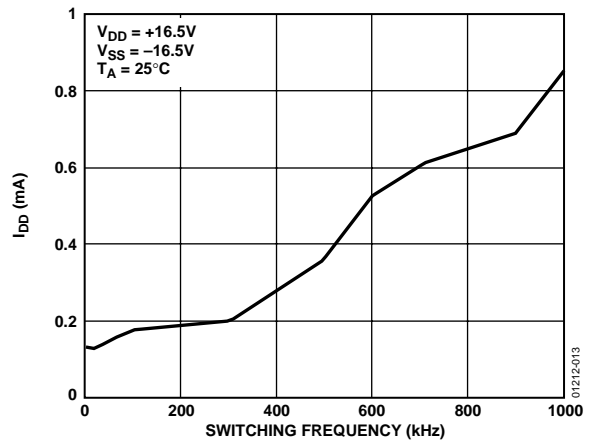


Figure 13.  $I_{DD}$  as a Function of Switching Frequency

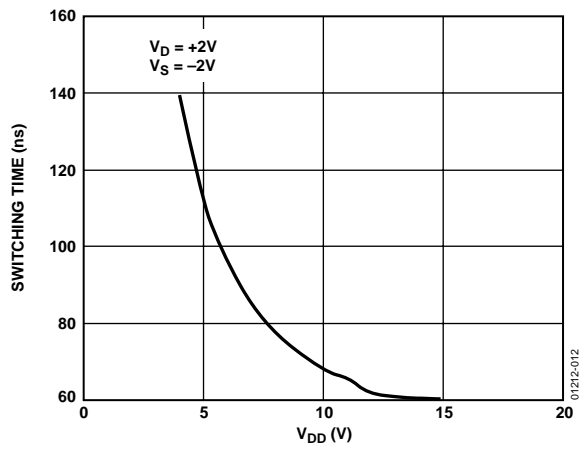


Figure 12. Switching Time as a Function of  $V_D$

## TEST CIRCUITS

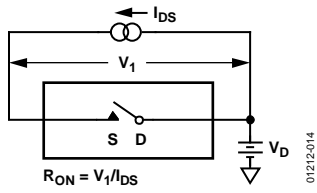


Figure 14. On Resistance

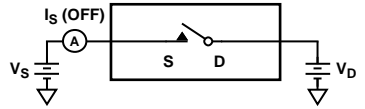


Figure 15. Off Leakage

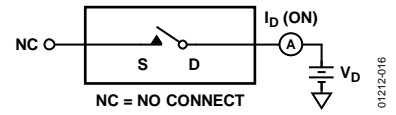


Figure 16. On Leakage

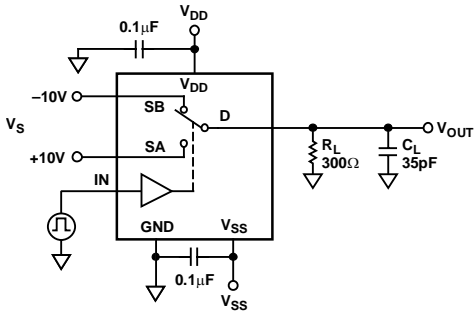


Figure 17. Switching Times

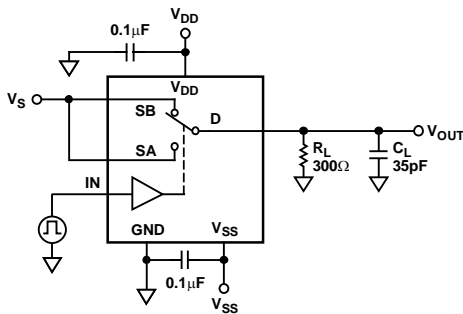


Figure 18. Break-Before-Make Delay,  $t_{OPEN}$

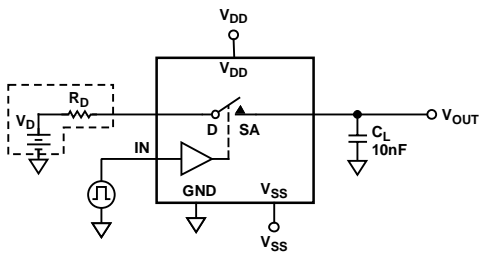


Figure 19. Charge Injection

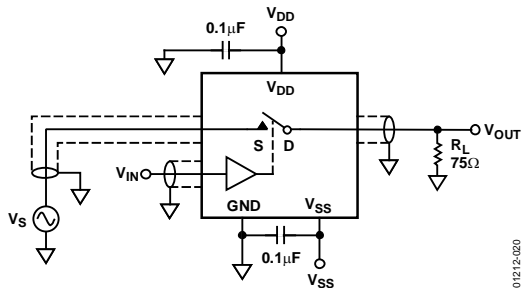


Figure 20. Off Isolation

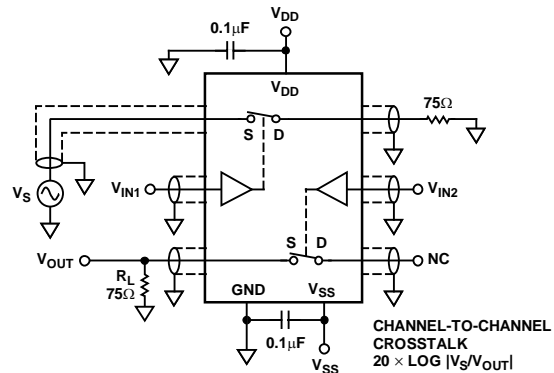


Figure 21. Channel-to-Channel Crosstalk

## APPLICATION INFORMATION

### ADG333A SUPPLY VOLTAGES

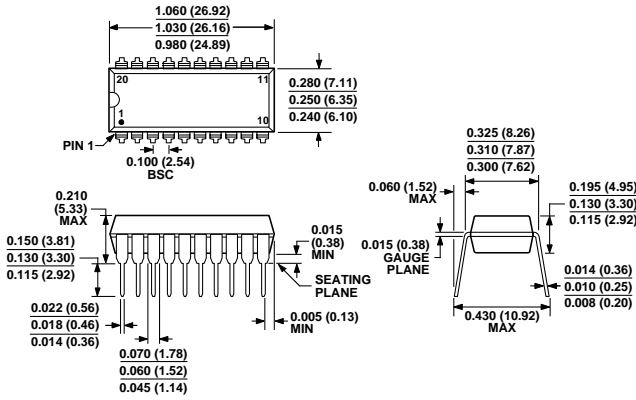
The ADG333A can operate from a dual or signal supply.  $V_{SS}$  should be connected to GND when operating with a single supply. When using a dual supply, the ADG333A can also operate with unbalanced supplies; for example  $V_{DD} = 20\text{ V}$  and  $V_{SS} = -5\text{ V}$ . The only restrictions are that  $V_{DD}$  to GND must not exceed 30 V,  $V_{SS}$  to GND must not drop below  $-30\text{ V}$ , and  $V_{DD}$  to  $V_{SS}$  must not exceed +44 V. It is important to remember that the ADG333A supply voltage directly affects the input signal range, the switch on resistance and the switching times of the part. The effects of the power supplies on these characteristics can be clearly seen from the Typical Performance Characteristics curves.

### POWER SUPPLY SEQUENCING

When using CMOS devices, care must be taken to ensure correct power-supply sequencing. Incorrect power-supply sequencing can result in the device being subjected to stresses beyond those listed in the Absolute Maximum Ratings. This is also true for the ADG333A. Always turn on  $V_{DD}$  first, followed by  $V_{SS}$  and the logic signals. An external signal within the maximum specified ratings can then be safely presented to the source or drain of the switch

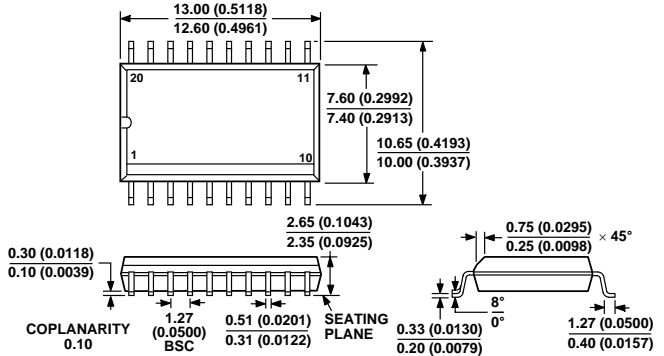
# ADG333A

## OUTLINE DIMENSIONS



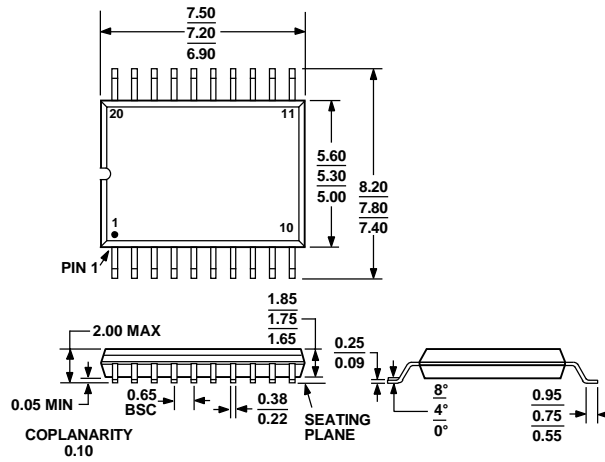
COMPLIANT TO JEDEC STANDARDS MS-001-AD  
 CONTROLLING DIMENSIONS ARE IN INCHES; MILLIMETER DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF INCH EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN. CORNER LEADS MAY BE CONFIGURED AS WHOLE OR HALF LEADS.

Figure 22. 20-Lead Plastic Dual In-Line Package [PDIP] Narrow Body (N-20)  
 Dimensions shown in inches and (millimeters)



COMPLIANT TO JEDEC STANDARDS MS-013AC  
 CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN

Figure 23. 20-Lead Standard Small Outline Package [SOIC] Wide Body (R-20)  
 Dimensions shown in millimeters and (inches)



COMPLIANT TO JEDEC STANDARDS MO-150AE

Figure 24. 20-Lead Shrink Small Outline Package [SSOP] (RS-20)  
 Dimensions shown in millimeters

## ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option
ADG333ABN	-40°C to +85°C	20-Lead Plastic Dual In-Line Package (PDIP)	N-20
ADG333ABR	-40°C to +85°C	20-Lead Standard Small Outline Package (SOIC)	R-20
ADG333ABR-REEL	-40°C to +85°C	20-Lead Standard Small Outline Package (SOIC)	R-20
ADG333ABRZ <sup>1</sup>	-40°C to +85°C	20-Lead Standard Small Outline Package (SOIC)	R-20
ADG333ABRZ-REEL <sup>1</sup>	-40°C to +85°C	20-Lead Standard Small Outline Package (SOIC)	R-20
ADG333ABRS	-40°C to +85°C	20-Lead Shrink Small Outline Package (SSOP)	RS-20
ADG333ABRS-REEL	-40°C to +85°C	20-Lead Shrink Small Outline Package (SSOP)	RS-20
ADG333ABRSZ <sup>1</sup>	-40°C to +85°C	20-Lead Shrink Small Outline Package (SSOP)	RS-20
ADG333ABRSZ-REEL <sup>1</sup>	-40°C to +85°C	20-Lead Shrink Small Outline Package (SSOP)	RS-20

<sup>1</sup> Z = Pb-free part.

## Данный компонент на территории Российской Федерации

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Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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